半导体物理

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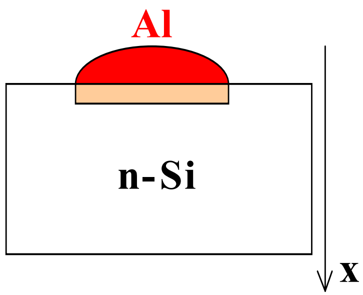
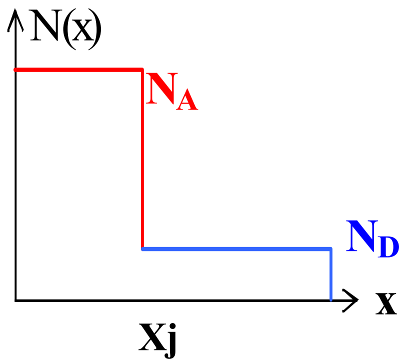
第八章 p-n结

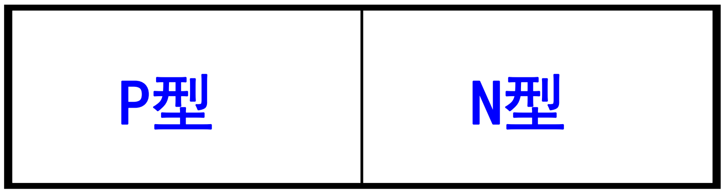
8.1 平衡p-n结特性1

8.1.1 p-n结的形成及杂质分布

一合金法





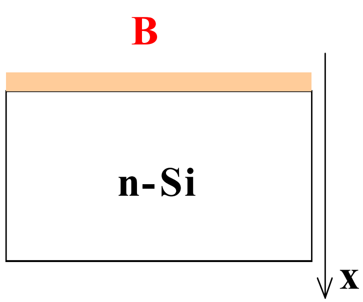


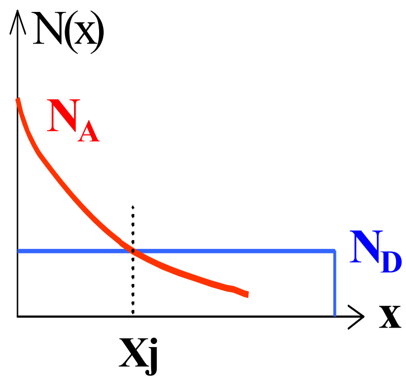
突变结

$N_A >> N_D$ $\quad p^+ - n$

$N_D >> N_A$ $\quad n^+ - p$

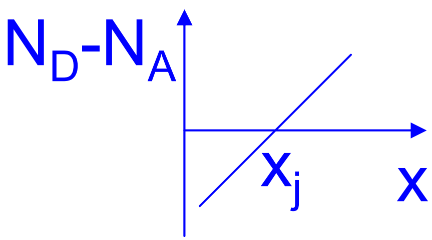
一扩散法





$x < x_j \quad x > x_j$

$N_A > N_D \quad N_A < N_D$

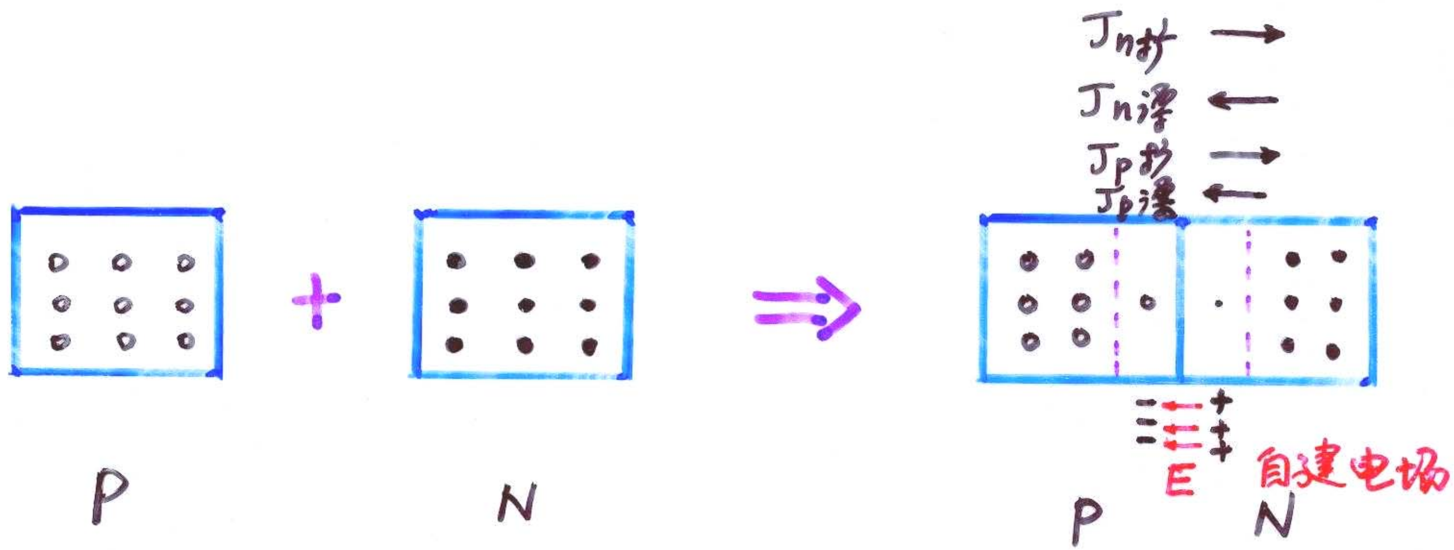


线性缓变结

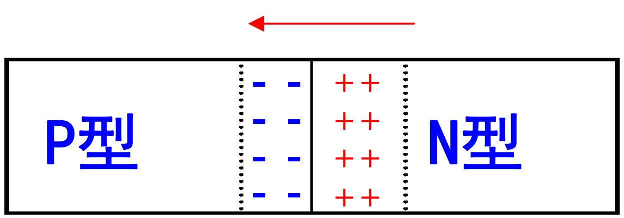
$$N_D - N_A = \alpha_j (x - x_j)$$

8.1 平衡p-n结特性2

8.1.2 空间电荷区



载流子浓度梯度 → 扩散 → 破坏电中性→ 自建电场 → 漂移电流 → 动态平衡→ 零净电流



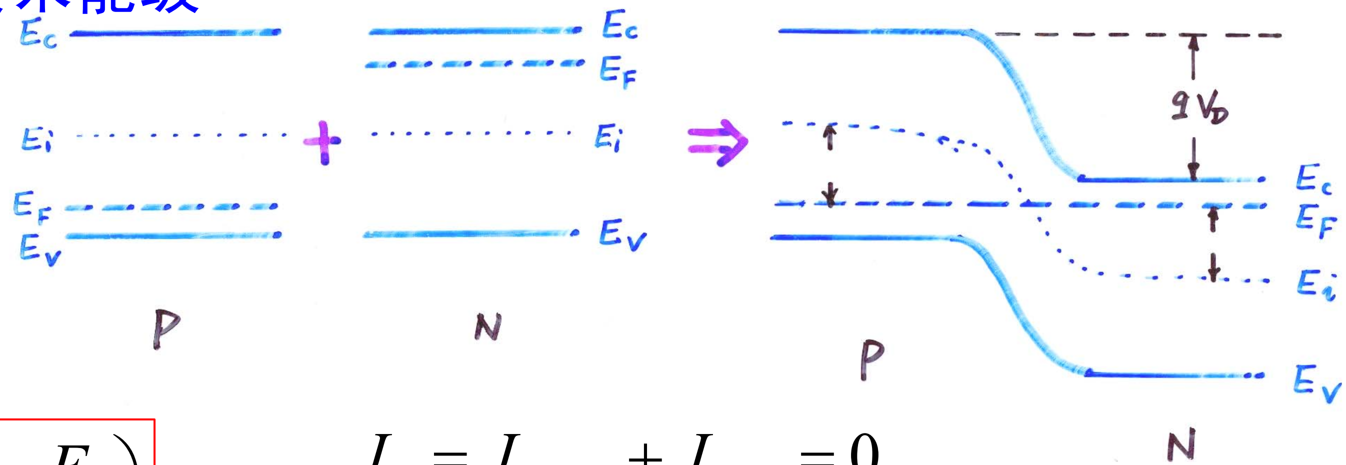
$$J_n = J_{n,diff} + J_{n,dr} = 0$$

$$J_p = J_{p,diff} + J_{p,dr} = 0$$

8.1 平衡p-n结特性3

8.1.3 平衡p-n结能带图

—平衡p-n结中费米能级



$$\boxed{n_0 = n_i \exp\left(\frac{E_F - E_i}{kT}\right)}$$

$$J_n = J_{n,diff} + J_{n,dr} = 0$$

$$J_n = qn_0\mu_n E + qD_n \frac{dn_0}{dx}$$

$$\frac{dn_0}{dx} = -n_0 \frac{1}{kT}\frac{dE_i}{dx} + n_0 \frac{1}{kT}\frac{dE_F}{dx}$$

$$\frac{dE_i}{dx} = -q\frac{dV(x)}{dx} = qE$$

电场

$$\frac{dn_0}{dx} = -n_0 \frac{qE}{kT} + n_0 \frac{1}{kT}\frac{dE_F}{dx}$$

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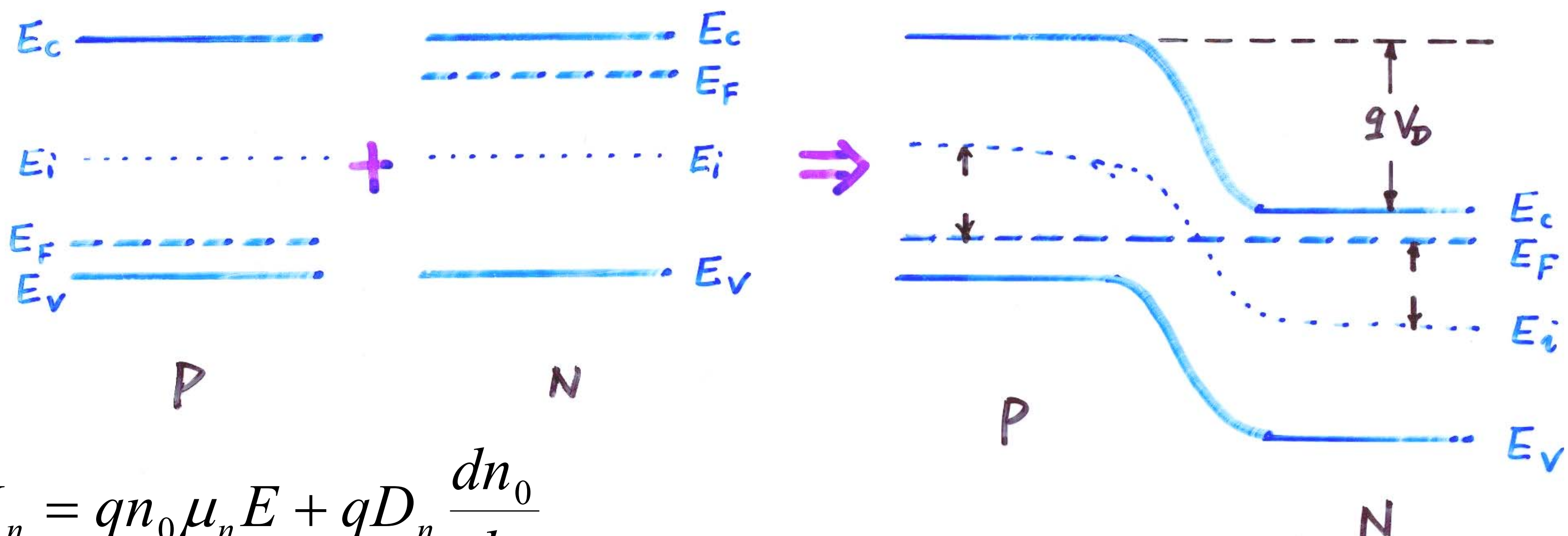
8.1.3 平衡p-n结能带图

—平衡p-n结中费米能级



$$J_n = qn_0\mu_n E + qD_n \frac{dn_0}{dx}$$

$$\frac{dn_0}{dx} = -n_0 \frac{qE}{kT} + n_0 \frac{1}{kT}\frac{dE_F}{dx}$$

$$J_n = \cancel{qn_0\mu_n E - qD_n n_0 \frac{qE}{kT}} + n_0 \frac{qD_n}{kT}\frac{dE_F}{dx} = 0 \longrightarrow \boxed{\frac{dE_F}{dx} = 0}$$

8.1 平衡p-n结特性5

8.1.4 p-n结接触电势差

$$\boxed{qV_D = E_{F(n)} - E_{F(p)}}$$

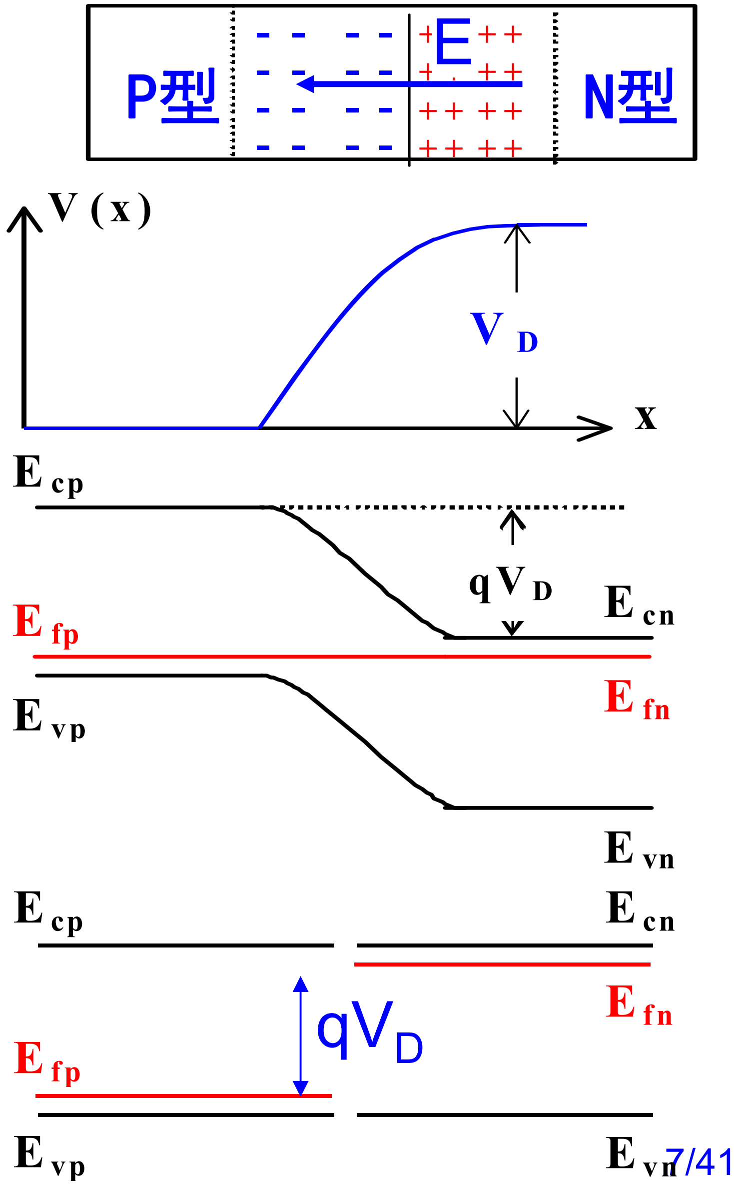
$$\left\{\begin{aligned} E_{F(n)} &= E_i + kT\ln\left(N_D/n_i\right) \\ E_{F(p)} &= E_i - kT\ln\left(N_A/n_i\right) \end{aligned}\right.$$

$$\boxed{V_D = \frac{kT}{q}\ln\left(\frac{N_A N_D}{n_i^2}\right)}$$

例子：$N_A = 10^{17}\ \mathrm{cm}^{-3}$，$N_D = 10^{15}\ \mathrm{cm}^{-3}$

Si $V_D \approx 0.7\ \mathrm{V}$

Ge $V_D \approx 0.3\ \mathrm{V}$



8.1 平衡p-n结特性6

8.1.5 p-n结的载流子分布

$$n(x)=N_C\exp\left(-\frac{E_C(x)-E_f}{kT}\right)$$

$$+E_{cn}-E_{cn}$$

$$n(x)=n_{n0}\exp\left(-\frac{E_c(x)-E_{cn}}{kT}\right)$$

$$E_c(x)-E_{cn}=qV_D-qV(x)$$

$$n(-x_p)=n_{n0}\exp\left(-\frac{E_{cp}-E_{cn}}{kT}\right)=n_{n0}\exp\left(-\frac{qV_D}{kT}\right)=n_{p0}$$

$$\boxed{n(x)=n_{p0}\exp\left[\frac{qV(x)}{kT}\right]}$$

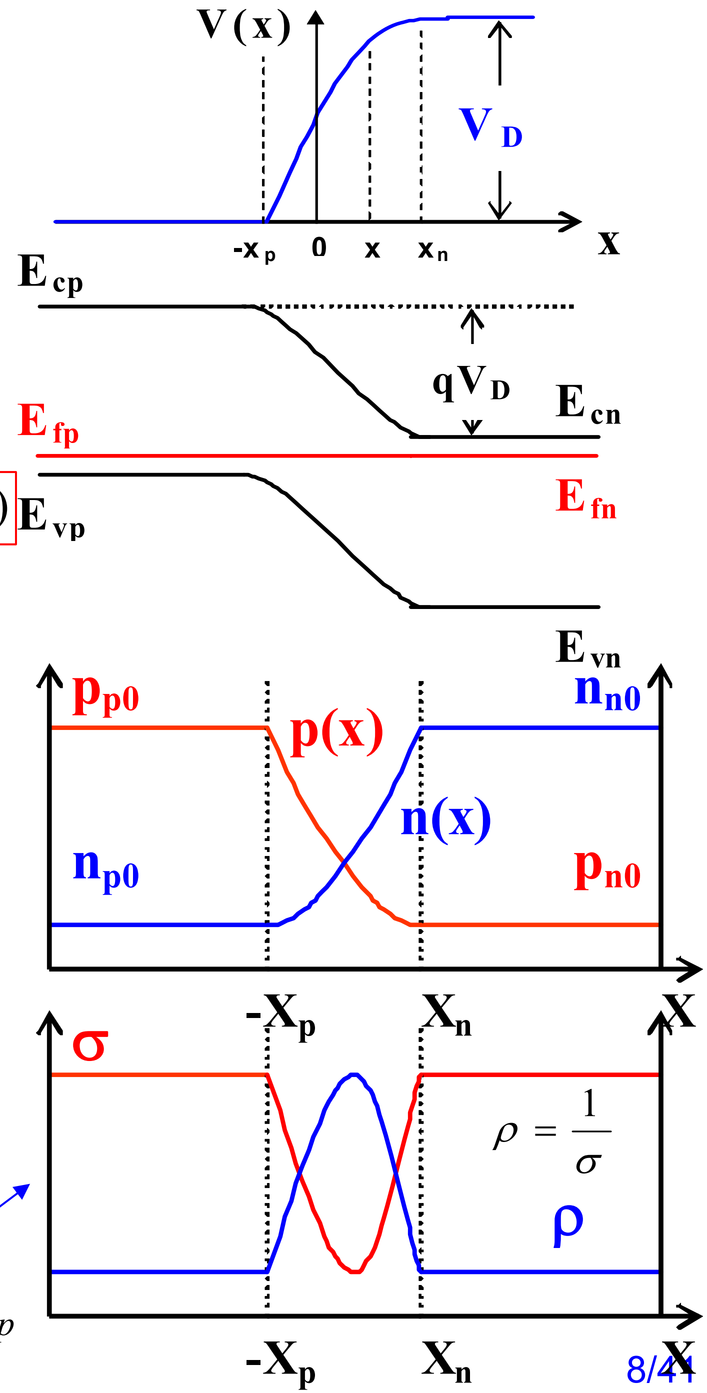
$$E_{Vp}-E_V(x)=qV(x)$$

$$p(x)=N_V\exp\left(-\frac{E_f-E_V(x)}{kT}\right)=p_{p0}\exp\left(-\frac{E_{Vp}-E_V(x)}{kT}\right)$$

$$p(x_n)=p_{p0}\exp\left(-\frac{E_{vp}-E_{vn}}{kT}\right)=p_{p0}\exp\left(-\frac{qV_D}{kT}\right)=p_{n0}$$

$$\boxed{p(x)=p_{p0}\exp\left[-\frac{qV(x)}{kT}\right]}$$

$$\sigma=qn\mu_n+qp\mu_p$$



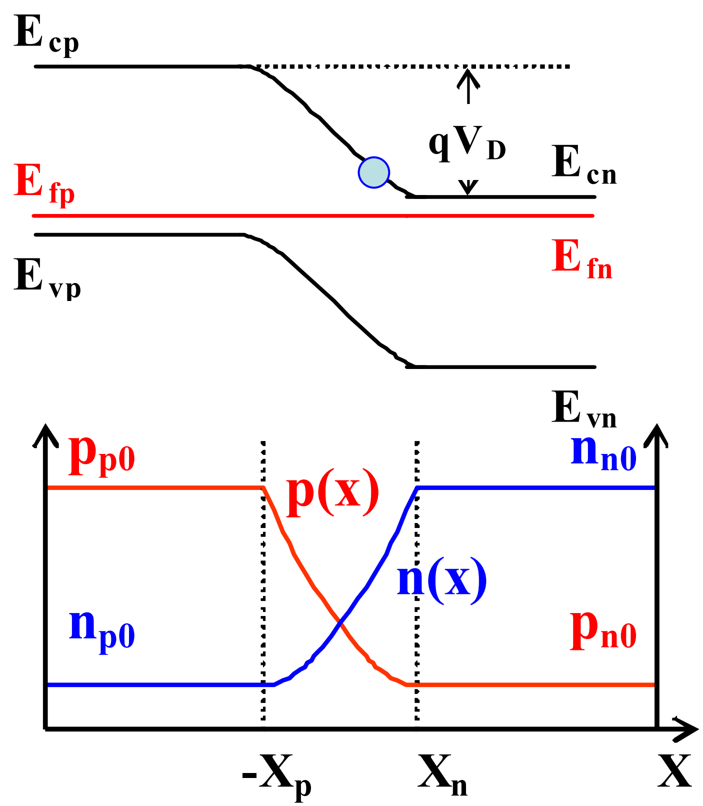
8.1 平衡p-n结特性7

8.1.5 p-n结的载流子分布

—势垒区中的载流子浓度估算

$$\boxed{n(x) = n_{p0}\exp\left[\frac{qV(x)}{kT}\right] = n_{n0}\exp\left[\frac{qV(x)-qV_D}{kT}\right]}$$

$$\boxed{p(x) = p_{p0}\exp\left[-\frac{qV(x)}{kT}\right]}$$



若位置x满足 $E_c(x) = E_{cn} + 0.1eV \longrightarrow$

$$V(x) = V_D - 0.1eV$$

$T = 300K$

$V_D = 0.7eV$

$$\longrightarrow n(x) = n_{n0}\exp\left[-\frac{0.1}{0.026}\right] \approx \frac{N_D}{50} \quad p(x) = p_{p0}\exp\left[-\frac{0.6}{0.026}\right] \approx 10^{-10}N_A$$

耗尽层近似：势垒区中载流子浓度可以忽略，
空间电荷密度就等于电离杂质浓度